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SiM3L1xx

High-Performance, Low-Power, 32-Bit Precision32™ MCU Family with up to 256 kB of Flash

32-bit ARM Cortex-M3 CPU

- 50 MHz maximum frequency
- Single-cycle multiplication, hardware division support
- Nested vectored interrupt control (NVIC) with 8 priority levels

Memory

- 32–256 kB flash, in-system programmable
- 8–32 kB SRAM with configurable low power retention

Clock Sources

- Internal oscillator with PLL: 23–50 MHz
- Low power internal oscillator: 20 MHz
- Low frequency internal oscillator (LFO): 16.4 kHz
- External real-time clock (RTC) crystal oscillator
- External oscillator: Crystal, RC, C, CMOS clock

Power Management

- Three adjustable low drop-out (LDO) regulators
- Power-on reset circuit and brownout detectors
- DC-DC buck converter allows dynamic voltage scaling for maximum efficiency (250 mW output)
- Multiple power modes supported for low power optimization

Low Power Features

- 75 nA typical current in Power Mode 8
- Low-current RTC (180 nA from LFO, 300 nA from crystal)
- 4 µs wakeup, register state retention and no reset required from lowest power mode
- 175 µA/MHz at 3.6 V executing from flash
- 140 µA/MHz at 3.6 V executing from SRAM
- Specialized on-chip charge pump reduces power consumption
- Process/Voltage/Temperature (PVT) Monitor

5 V Tolerant Flexible I/O

- Up to 62 contiguous 5 V tolerant GPIO with one priority cross-bar providing flexibility in pin assignments

Temperature Range: –40 to +85 °C

Supply Voltage: 1.8 to 3.8 V

Analog Peripherals

- 12-Bit Analog-to-Digital Converter: Up to 250 ksps 12-bit mode or 1 Msps 10-bit mode
- 10-Bit Current-mode Digital-to-Analog Converter
- 2 x Low-current comparators

Digital and Communication Peripherals

- 1 x USART with IrDA and ISO7816 Smartcard support
- 1 x UART that operates in low power mode
- 2 x SPIs, 1 x I2C, 16/32-bit CRC
- 128/192/256-bit Hardware AES Encryption
- Encoder/Decoder: Manchester and Three-out-of-Six
- Integrated LCD Controller: up to 160 segments (40x4), auto-contrast and low power operation

Timers/Counters

- 3 x 32-bit or 6 x 16-bit timers with capture/compare
- 16-bit, 6-channel counter with capture/compare/PWM and dead-time controller with differential outputs
- 16-bit low power timer/advanced capture counter operational in the lowest power mode
- 32-bit real time clock (RTC) with multiple alarms
- Watchdog timer
- Low power mode advanced capture counter (ACCTR)

Data Transfer Peripherals

- 10-Channel DMA Controller
- 3 Channel Data Transfer Manager manages complex DMA transfers without core intervention

On-Chip Debugging

- Serial wire debug (SWD) with serial wire viewer (SWV) or JTAG (no boundary scan) allow debug and programming
- Cortex-M3 embedded trace macrocell (ETM)

Package Options

- QFN options: 40-pin (6 x 6 mm), 64-pin (9 x 9 mm)
- TQFP options: 64-pin (10 x 10 mm), 80-pin (12 x 12 mm)

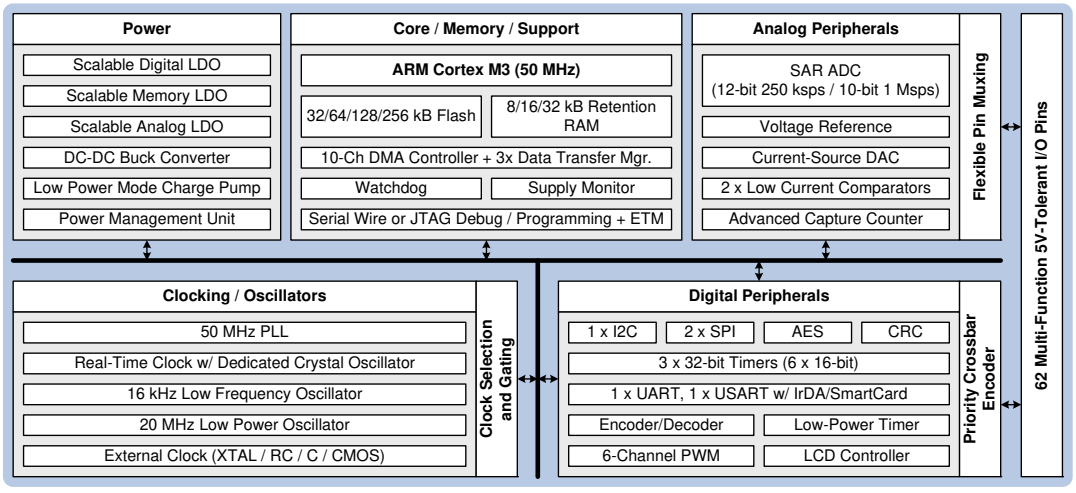

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Table of Contents

1. Related Documents and Conventions

1.1. Related Documents

This data sheet accompanies several documents to provide the complete description of the SiM3L1xx devices.

1.1.1. SiM3L1xx Reference Manual

The Silicon Laboratories SiM3L1xx Reference Manual provides the detailed description for each peripheral on the SiM3L1xx devices.

1.1.2. Hardware Access Layer (HAL) API Description

The Silicon Laboratories Hardware Access Layer (HAL) API provides C-language functions to modify and read each bit in the SiM3L1xx devices. This description can be found in the SiM3xxxx HAL API Reference Manual.

1.1.3. ARM Cortex-M3 Reference Manual

The ARM-specific features like the Nested Vectored Interrupt Controller are described in the ARM Cortex-M3 reference documentation. The online reference manual can be found here:
http://infocenter.arm.com/help/topic/com.arm.doc.subset.cortexm3/index.html#cortexm3.

1.2. Conventions

The block diagrams in this document use the following formatting conventions:

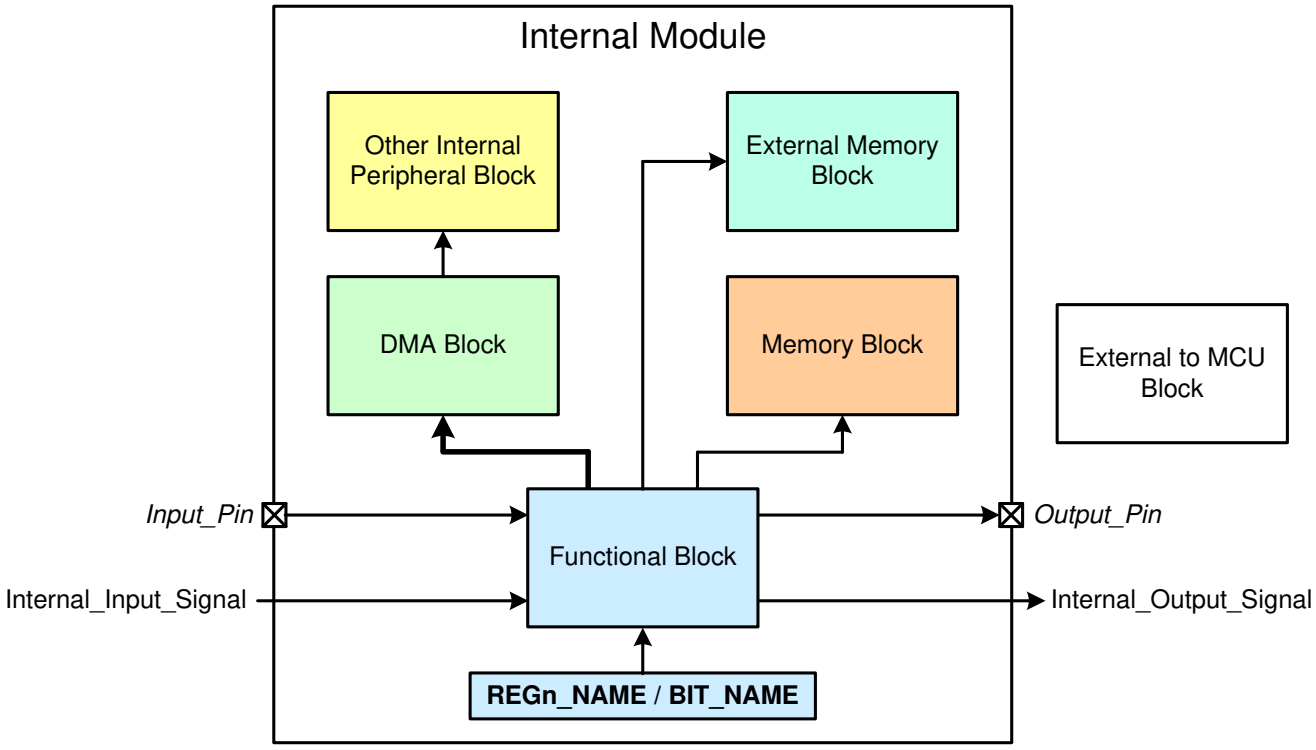

Figure 1.1. Block Diagram Conventions

2. Typical Connection Diagrams

This section provides typical connection diagrams for SiM3L1xx devices.

2.1. Power

Figure 2.1 shows a typical connection diagram for the power pins of the SiM3L1xx devices when the dc-dc buck converter is not used.

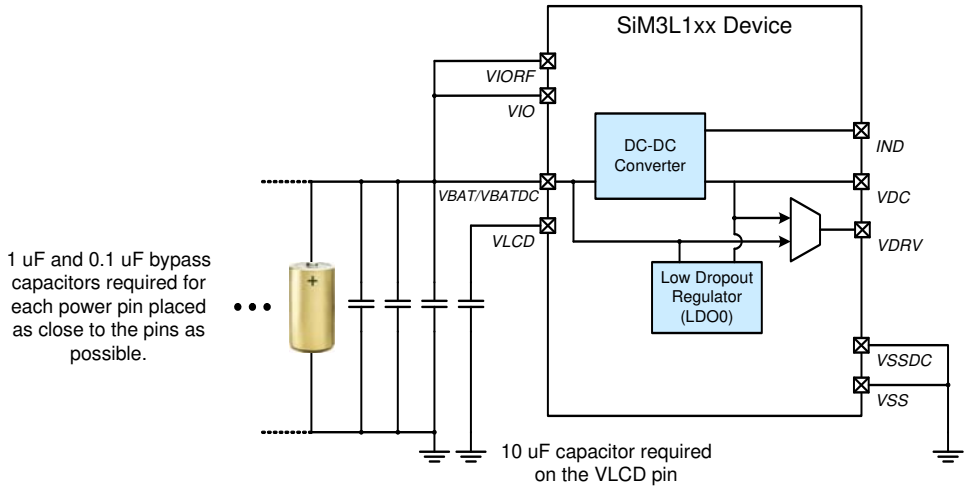

Figure 2.1. Connection Diagram with DC-DC Converter Unused

Figure 2.2 shows a typical connection diagram for the power pins of the SiM3L1xx devices when the internal dc-dc buck converter is in use and I/O are powered directly from the battery.

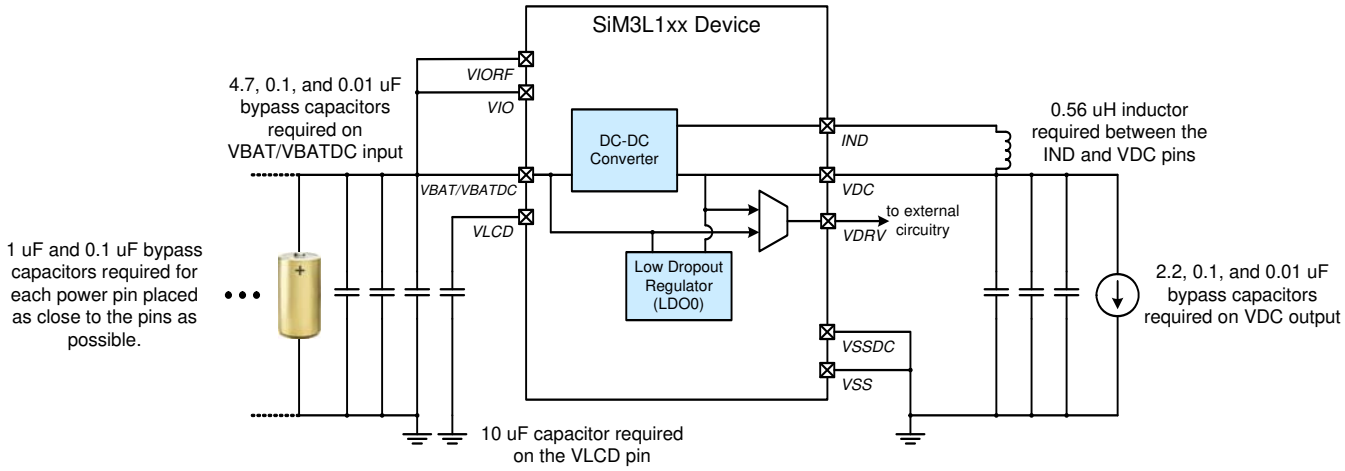

Figure 2.2. Connection Diagram with DC-DC Converter Used and I/O Powered from Battery

Figure 2.3 shows a typical connection diagram for the power pins of the SiM3L1xx devices when used with an external radio device like the Silicon Labs EZRadio® or EZRadioPRO® devices.

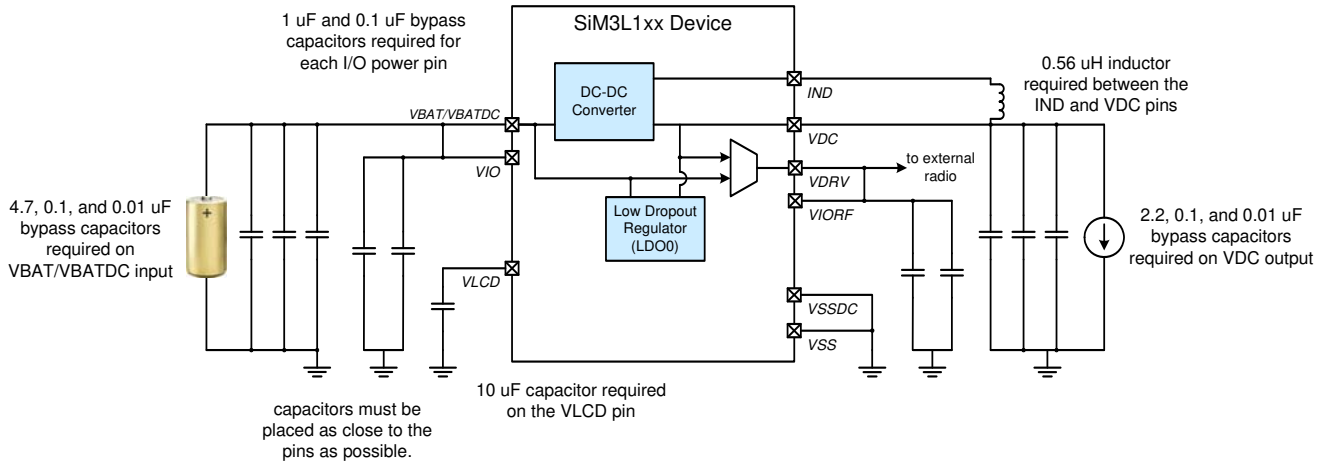

Figure 2.3. Connection Diagram with External Radio Device

Figure 2.4 shows a typical connection diagram for the power pins of the SiM3L1xx devices when the dc-dc buck converter is used and the I/O are powered separately.

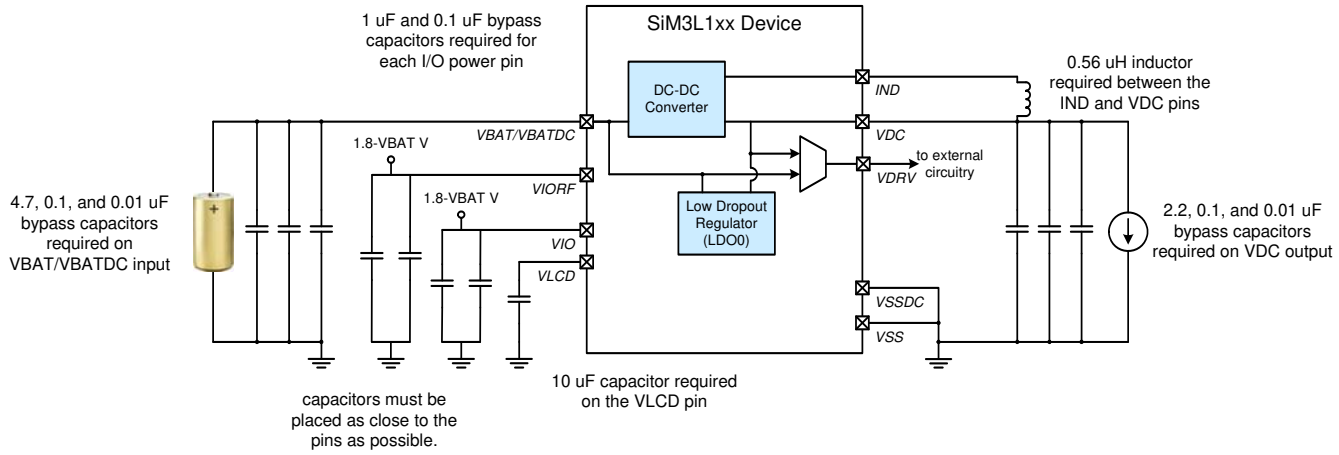

Figure 2.4. Connection Diagram with DC-DC Converter Used and I/O Powered Separately

3. Electrical Specifications

3.1. Electrical Characteristics

All electrical parameters in all Tables are specified under the conditions listed in Table 3.1, unless stated otherwise.

Table 3.1. Recommended Operating Conditions

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Operating Supply Voltage on VBAT/VBATDC	V_{BAT}		1.8	—	3.8	V
Operating Supply Voltage on VDC	V_{DC}		1.25	—	3.8	V
Operating Supply Voltage on VDRV	V_{DRV}		1.25	—	3.8	V
Operating Supply Voltage on VIO	V_{IO}		1.8	—	V_{BAT}	V
Operation Supply Voltage on VIORF	V_{IORF}		1.8	—	V_{BAT}	V
Operation Supply Voltage on VLCD	V_{LCD}		1.8	—	3.8	V
System Clock Frequency (AHB)	f_{AHB}		0	—	50	MHz
Peripheral Clock Frequency (APB)	f_{APB}		0	—	50	MHz
Operating Ambient Temperature	T_A		–40	—	+85	°C
Operating Junction Temperature	T_J		–40	—	105	°C
Note: All voltages with respect to V_{SS}.						

Table 3.2. Power Consumption

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Digital Core Supply Current						
Normal Mode[1,2,3,4]—Full speed with code executing from flash, peripheral clocks ON	I_{BAT}	F_{AHB} = 49 MHz, F_{APB} = 24.5 MHz	—	17.5	18.9	mA
		F_{AHB} = 20 MHz, F_{APB} = 10 MHz	—	6.7	7.2	mA
		F_{AHB} = 2.5 MHz, F_{APB} = 1.25 MHz	—	1.15	1.4	mA
Normal Mode[1,2,3,4]—Full speed with code executing from flash, peripheral clocks OFF	I_{BAT}	F_{AHB} = 49 MHz, F_{APB} = 24.5 MHz	—	13.3	14.5	mA
		F_{AHB} = 20 MHz, F_{APB} = 10 MHz	—	5.4	5.9	mA
		F_{AHB} = 2.5 MHz, F_{APB} = 1.25 MHz	—	980	1.2	µA
Normal Mode[1,2,3,4]—Full speed with code executing from flash, LDOs powered by dc-dc at 1.9 V, peripheral clocks OFF	I_{BAT}	F_{AHB} = 49 MHz, F_{APB} = 24.5 MHz V_{BAT} = 3.3 V	—	9.7	—	mA
		F_{AHB} = 49 MHz, F_{APB} = 24.5 MHz V_{BAT} = 3.8 V	—	8.65	—	mA
		F_{AHB} = 20 MHz, F_{APB} = 10 MHz V_{BAT} = 3.3 V	—	4.15	—	mA
		F_{AHB} = 20 MHz, F_{APB} = 10 MHz V_{BAT} = 3.8 V	—	3.9	—	mA

Notes:

1. Currents are additive. For example, where I_{BAT} is specified and the mode is not mutually exclusive, enabling the functions increases supply current by the specified amount.
2. Includes all peripherals that cannot have clocks gated in the Clock Control module.
3. Includes LDO and PLL0OSC (>20 MHz) or LPOSC0 (≤20 MHz) supply current.
4. Internal Digital and Memory LDOs scaled to optimal output voltage.
5. Flash AHB clock turned off.
6. Running from internal LFO, Includes LFO supply current.
7. LCD0 current does not include switching currents for external load.
8. IDAC output current not included.
9. Does not include LC tank circuit.
10. Does not include digital drive current or pullup current for active port I/O. Unloaded I_{VIO} is included in all I_{BAT} PM8 production test measurements.

Table 3.2. Power Consumption (Continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Power Mode 1[1,2,3,4]—Full speed with code executing from RAM, peripheral clocks ON	I_{BAT}	F_{AHB} = 49 MHz, F_{APB} = 24.5 MHz	—	13.4	16.6	mA
		F_{AHB} = 20 MHz, F_{APB} = 10 MHz	—	4.7	—	mA
		F_{AHB} = 2.5 MHz, F_{APB} = 1.25 MHz	—	810	—	µA
Power Mode 1[1,2,3,4]—Full speed with code executing from RAM, peripheral clocks OFF	I_{BAT}	F_{AHB} = 49 MHz, F_{APB} = 24.5 MHz	—	9.4	12.5	mA
		F_{AHB} = 20 MHz, F_{APB} = 10 MHz	—	3.3	—	mA
		F_{AHB} = 2.5 MHz, F_{APB} = 1.25 MHz	—	630	—	µA
Power Mode 1[1,2,3,4]—Full speed with code executing from RAM, LDOs powered by dc-dc at 1.9 V, peripheral clocks OFF	I_{BAT}	F_{AHB} = 49 MHz, F_{APB} = 24.5 MHz V_{BAT} = 3.3 V	—	7.05	—	mA
		F_{AHB} = 49 MHz, F_{APB} = 24.5 MHz V_{BAT} = 3.8 V	—	6.3	—	mA
		F_{AHB} = 20 MHz, F_{APB} = 10 MHz V_{BAT} = 3.3 V	—	2.75	—	mA
		F_{AHB} = 20 MHz, F_{APB} = 10 MHz V_{BAT} = 3.8 V	—	2.6	—	mA
Power Mode 2[1,2,3,4,5]—Core halted with peripheral clocks ON	I_{BAT}	F_{AHB} = 49 MHz, F_{APB} = 24.5 MHz	—	7.6	11.3	mA
		F_{AHB} = 20 MHz, F_{APB} = 10 MHz	—	2.75	—	mA
		F_{AHB} = 2.5 MHz, F_{APB} = 1.25 MHz	—	575	—	µA

Notes:

1. Currents are additive. For example, where I_{BAT} is specified and the mode is not mutually exclusive, enabling the functions increases supply current by the specified amount.
2. Includes all peripherals that cannot have clocks gated in the Clock Control module.
3. Includes LDO and PLL0OSC (>20 MHz) or LPOSC0 (≤20 MHz) supply current.
4. Internal Digital and Memory LDOs scaled to optimal output voltage.
5. Flash AHB clock turned off.
6. Running from internal LFO, Includes LFO supply current.
7. LCD0 current does not include switching currents for external load.
8. IDAC output current not included.
9. Does not include LC tank circuit.
10. Does not include digital drive current or pullup current for active port I/O. Unloaded I_{VIO} is included in all I_{BAT} PM8 production test measurements.

Table 3.2. Power Consumption (Continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Power Mode 2[1,2,3,4,5]—Core halted with only Port I/O clocks on (wake from pin).	I_{BAT}	F_{AHB} = 49 MHz, F_{APB} = 24.5 MHz	—	4	7.2	mA
		F_{AHB} = 20 MHz, F_{APB} = 10 MHz	—	1.47	—	mA
		F_{AHB} = 2.5 MHz, F_{APB} = 1.25 MHz	—	430	—	µA
Power Mode 3[1,2,6]—Fast-Wake Mode (PM3CLKEN = 1)	I_{BAT}	V_{BAT} = 3.8 V	—	320	530	µA
		V_{BAT} = 1.8 V	—	225	—	µA
Power Mode 4[1,2,4,6]—Slower clock speed with code executing from flash, peripheral clocks ON	I_{BAT}	F_{AHB} = F_{APB} = 16 kHz, V_{BAT} = 3.8 V	—	385	640	µA
		F_{AHB} = F_{APB} = 16 kHz, V_{BAT} = 1.8 V	—	330	—	µA
Power Mode 5[1,2,4,6]—Slower clock speed with code executing from RAM, peripheral clocks ON	I_{BAT}	F_{AHB} = F_{APB} = 16 kHz, V_{BAT} = 3.8 V	—	320	490	µA
		F_{AHB} = F_{APB} = 16 kHz, V_{BAT} = 1.8 V	—	275	—	µA
Power Mode 6[1,2,4,6]—Core halted with peripheral clocks ON	I_{BAT}	F_{AHB} = F_{APB} = 16 kHz, V_{BAT} = 3.8 V	—	315	490	µA
		F_{AHB} = F_{APB} = 16 kHz, V_{BAT} = 1.8 V	—	270	—	µA
Power Mode 8[1,2]—Low Power Sleep, powered through VBAT, VIO, and VIORF at 2.4 V, 32kB of retention RAM	I_{BAT}	RTC Disabled, T_A = 25 °C	—	75	400	nA
		RTC w/ 16.4 kHz LFO, T_A = 25 °C	—	360	—	nA
		RTC w/ 32.768 kHz Crystal, T_A = 25 °C	—	670	—	nA

Notes:
1. Currents are additive. For example, where I_{BAT} is specified and the mode is not mutually exclusive, enabling the functions increases supply current by the specified amount.
2. Includes all peripherals that cannot have clocks gated in the Clock Control module.
3. Includes LDO and PLL0OSC (>20 MHz) or LPOSC0 (≤20 MHz) supply current.
4. Internal Digital and Memory LDOs scaled to optimal output voltage.
5. Flash AHB clock turned off.
6. Running from internal LFO, Includes LFO supply current.
7. LCD0 current does not include switching currents for external load.
8. IDAC output current not included.
9. Does not include LC tank circuit.
10. Does not include digital drive current or pullup current for active port I/O. Unloaded I_{VIO} is included in all I_{BAT} PM8 production test measurements.

Table 3.2. Power Consumption (Continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Power Mode 8[1,2]—Low Power Sleep, powered by the low power mode charge pump, 32kB of retention RAM	I_{BAT}	RTC w/ 16.4 kHz LFO, V_{BAT} = 2.4 V, T_A = 25 °C	—	180	—	nA
		RTC w/ 32.768 kHz Crystal, V_{BAT} = 2.4 V, T_A = 25 °C	—	300	—	nA
		RTC w/ 16.4 kHz LFO, V_{BAT} = 3.8 V, T_A = 25 °C	—	245	—	nA
		RTC w/ 32.768 kHz Crystal, V_{BAT} = 3.8 V, T_A = 25 °C	—	390	—	nA
Unloaded V_{IO} and V_{IORF} Current[10]	I_{VIO}		—	2	—	nA
Power Mode 8 Peripheral Currents						
UART0	I_{UART0}	V_{BAT} = 3.8 V, T_A = 25 °C	—	195	600	nA
		V_{BAT} = 2.4 V, T_A = 25 °C	—	120	—	nA
LCD0[7], No segments active	I_{LCD0}	V_{BAT} = 3.8 V, T_A = 25 °C	—	495	660	nA
		V_{BAT} = 2.4 V, T_A = 25 °C	—	395	—	nA
LCD0[7], All (4 x 40) segments active	I_{LCD0}	V_{BAT} = 3.8 V, T_A = 25 °C	—	800	—	nA
		V_{BAT} = 2.4 V, T_A = 25 °C	—	580	—	nA
Advanced Capture Counter (ACCTR0), LC Single-Ended Mode, Relative to Sampling Frequency[9]	I_{ACCTR}	V_{BAT} = 2.4 V, T_A = 25 °C, CPMD = 01	—	1.11	—	nA/Hz
		V_{BAT} = 3.8 V, T_A = 25 °C, CPMD = 01	—	1.44	—	nA/Hz
		V_{BAT} = 2.4 V, T_A = 25 °C, CPMD = 10	—	1.45	—	nA/Hz
		V_{BAT} = 3.8 V, T_A = 25 °C, CPMD = 10	—	1.82	—	nA/Hz
		V_{BAT} = 2.4 V, T_A = 25 °C, CPMD = 11	—	2.15	—	nA/Hz
		V_{BAT} = 3.8 V, T_A = 25 °C, CPMD = 11	—	2.54	—	nA/Hz

Notes:

1. Currents are additive. For example, where I_{BAT} is specified and the mode is not mutually exclusive, enabling the functions increases supply current by the specified amount.
2. Includes all peripherals that cannot have clocks gated in the Clock Control module.
3. Includes LDO and PLL0OSC (>20 MHz) or LPOSC0 (≤20 MHz) supply current.
4. Internal Digital and Memory LDOs scaled to optimal output voltage.
5. Flash AHB clock turned off.
6. Running from internal LFO, Includes LFO supply current.
7. LCD0 current does not include switching currents for external load.
8. IDAC output current not included.
9. Does not include LC tank circuit.
10. Does not include digital drive current or pullup current for active port I/O. Unloaded I_{VIO} is included in all I_{BAT} PM8 production test measurements.

Table 3.2. Power Consumption (Continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Advanced Capture Counter (ACCTR0), LC Dual or Quadrature Mode, Relative to Sampling Frequency[9]	I_{ACCTR}	V_{BAT} = 2.4 V, T_A = 25 °C, CPMD = 01	—	1.39	—	nA/Hz
		V_{BAT} = 3.8 V, T_A = 25 °C, CPMD = 01	—	1.89	—	nA/Hz
		V_{BAT} = 2.4 V, T_A = 25 °C, CPMD = 10	—	2.08	—	nA/Hz
		V_{BAT} = 3.8 V, T_A = 25 °C, CPMD = 10	—	2.59	—	nA/Hz
		V_{BAT} = 2.4 V, T_A = 25 °C, CPMD = 11	—	3.47	—	nA/Hz
		V_{BAT} = 3.8 V, T_A = 25 °C, CPMD = 11	—	4.03	—	nA/Hz
Analog Peripheral Supply Currents						
PLL0 Oscillator (PLL0OSC)	I_{PLLOSC}	Operating at 49 MHz	—	1.4	1.6	mA
Low-Power Oscillator (LPOSC0)	I_{LPOSC}	Operating at 20 MHz	—	25	—	µA
		Operating at 2.5 MHz	—	25	—	µA
Low-Frequency Oscillator (LFOSC0)	I_{LFOSC}	Operating at 16.4 kHz	—	190	310	nA
External Oscillator (EXTOSC0)	I_{EXTOSC}	FREQCN = 111	—	3.8	4.5	mA
		FREQCN = 110	—	840	960	µA
		FREQCN = 101	—	185	230	µA
		FREQCN = 100	—	65	80	µA
		FREQCN = 011	—	25	30	µA
		FREQCN = 010	—	10	13	µA
		FREQCN = 001	—	5	7	µA
		FREQCN = 000	—	3	5	µA

Notes:

1. Currents are additive. For example, where I_{BAT} is specified and the mode is not mutually exclusive, enabling the functions increases supply current by the specified amount.
2. Includes all peripherals that cannot have clocks gated in the Clock Control module.
3. Includes LDO and PLL0OSC (>20 MHz) or LPOSC0 (≤20 MHz) supply current.
4. Internal Digital and Memory LDOs scaled to optimal output voltage.
5. Flash AHB clock turned off.
6. Running from internal LFO, Includes LFO supply current.
7. LCD0 current does not include switching currents for external load.
8. IDAC output current not included.
9. Does not include LC tank circuit.
10. Does not include digital drive current or pullup current for active port I/O. Unloaded I_{VIO} is included in all I_{BAT} PM8 production test measurements.

Table 3.2. Power Consumption (Continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
SARADC0	I_{SARADC}	Sampling at 1 Msps, Internal VREF used	—	1.2	1.6	mA
		Sampling at 250 ksps, lowest power mode settings.	—	390	540	µA
Temperature Sensor	I_{TSENSE}		—	75	110	µA
Internal SAR Reference	I_{REFFS}	Normal Power Mode	—	680	—	µA
		Normal Power Mode	—	160	—	µA
VREF0	I_{REFP}		—	80	—	µA
Comparator 0 (CMP0), Comparator 1 (CMP1)	I_{CMP}	CMPMD = 11	—	0.5	2	µA
		CMPMD = 10	—	3	8	µA
		CMPMD = 01	—	10	16	µA
		CMPMD = 00	—	25	42	µA
IDAC0[8]	I_{IDAC}		—	70	100	µA
Voltage Supply Monitor (VMON0)	I_{VMON}		—	10	22	µA
Flash Current on VBAT						
Write Operation	$I_{FLASH-W}$		—	—	8	mA
Erase Operation	$I_{FLASH-E}$		—	—	15	mA

Notes:
1. Currents are additive. For example, where I_{BAT} is specified and the mode is not mutually exclusive, enabling the functions increases supply current by the specified amount.
2. Includes all peripherals that cannot have clocks gated in the Clock Control module.
3. Includes LDO and PLL0OSC (>20 MHz) or LPOSC0 (≤20 MHz) supply current.
4. Internal Digital and Memory LDOs scaled to optimal output voltage.
5. Flash AHB clock turned off.
6. Running from internal LFO, Includes LFO supply current.
7. LCD0 current does not include switching currents for external load.
8. IDAC output current not included.
9. Does not include LC tank circuit.
10. Does not include digital drive current or pullup current for active port I/O. Unloaded I_{VIO} is included in all I_{BAT} PM8 production test measurements.

Table 3.3. Power Mode Wake Up Times

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Power Mode 2 or 6 Wake Time	t_{PM2}		4	—	5	clocks
Power Mode 3 Fast Wake Time (using LFO as clock source)	t_{PM3FW}		—	425	—	µs
Power Mode 8 Wake Time	t_{PM8}		—	3.8	—	µs

Notes:
1. Wake times are specified as the time from the wake source to the execution phase of the first instruction following WFI. This includes latency to recognize the wake event and fetch the first instruction (assuming wait states = 0).

Table 3.4. Reset and Supply Monitor

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
V_{BAT} High Supply Monitor Threshold (VBATHITHEN = 1)	V_{VBATMH}	Early Warning	—	2.20	—	V
		Reset	1.95	2.05	2.1	V
V_{BAT} Low Supply Monitor Threshold (VBATHITHEN = 0)	V_{VBATML}	Early Warning	—	1.85	—	V
		Reset	1.70	1.75	1.77	V
Power-On Reset (POR) Threshold	V_{POR}	Rising Voltage on V_{BAT}	—	1.4	—	V
		Falling Voltage on V_{BAT}	0.8	1	1.3	V
V_{BAT} Ramp Time	t_{RMP}	Time to $V_{BAT} \geq$ 1.8 V	10	—	3000	µs
Reset Delay from POR	t_{POR}	Relative to $V_{BAT} \geq V_{POR}$	3	—	100	ms
Reset Delay from non-POR source	t_{RST}	Time between release of reset source and code execution	—	10	—	µs
$\overline{\text{RESET}}$ Low Time to Generate Reset	t_{RSTL}		50	—	—	ns
Missing Clock Detector Response Time (final rising edge to reset)	t_{MCD}	F_{AHB} > 1 MHz	—	0.5	1.5	ms
Missing Clock Detector Trigger Frequency	F_{MCD}		—	2.5	10	kHz
V_{BAT} Supply Monitor Turn-On Time	t_{MON}		—	2	—	µs

Table 3.5. On-Chip Regulators

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
DC-DC Buck Converter						
Input Voltage Range	V_{DCIN}		1.8	—	3.8	V
Input Supply to Output Voltage Differential (for regulation)	V_{DCREG}		0.45	—	—	V
Output Voltage Range	V_{DCOUT}		1.25	—	3.8	V
Output Voltage Accuracy	V_{DCACC}		—	±25	—	mV
Output Current	I_{DCOUT}		—	—	90	mA
Inductor Value[1]	L_{DC}		0.47	0.56	0.68	µH
Inductor Current Rating	I_{LDC}	I_{load} < 50 mA	450	—	—	mA
		I_{load} > 50 mA	550	—	—	mA
Output Capacitor Value	C_{DCOUT}		1	2.2	10	µF
Input Capacitor Value[2]	C_{DCIN}		—	4.7	—	µF
Load Regulation	R_{load}		—	0.03	—	mV/mA
Maximum DC Load Current During Startup	I_{DCMAX}		—	—	5	mA
Switching Clock Frequency	F_{DCCLK}		1.9	2.9	3.8	MHz
Local Oscillator Frequency	F_{DCOSC}		2.4	2.9	3.4	MHz
LDO Regulators						
Input Voltage Range[3]	V_{LDOIN}	Sourced from VBAT	1.8	—	3.8	V
		Sourced from VDC	1.9	—	3.8	V
Output Voltage Range[4]	V_{LDO}		0.8	—	1.9	V
LDO Output Voltage Accuracy	V_{LDOACC}		—	±25	—	mV
Output Settings in PM8 (All LDOs)	V_{LDO}	1.8 V ≤ V_{BAT} ≤ 2.9 V		1.5		V
		1.95 V ≤ V_{BAT} ≤ 3.5 V		1.8		V
		2.0 V ≤ V_{BAT} ≤ 3.8 V		1.9		V

Notes:

1. See reference manual for recommended inductors.
2. Recommended: X7R or X5R ceramic capacitors with low ESR. Example: Murata GRM21BR71C225K with ESR < 10 mΩ (@ frequency > 1 MHz).
3. Input voltage specification accounts for the internal LDO dropout voltage under the maximum load condition to ensure that the LDO output voltage will remain at a valid level as long as V_{LDOIN} is at or above the specified minimum.
4. The memory LDO output should always be set equal to or lower than the output of the analog LDO. When lowering both LDOs (for example to go into PM8 under low supply conditions), first adjust the memory LDO and then the analog LDO. When raising the output of both LDOs, adjust the analog LDO before adjusting the memory LDO.
5. Output range represents the programmable output range, and does not reflect the minimum voltage under all conditions. Dropout when the input supply is close to the output setting is normal, and accounted for.
6. Analog peripheral specifications assume a 1.8 V output on the analog LDO.

Table 3.5. On-Chip Regulators (Continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Memory LDO Output Setting[5]	V_{LDOMEM}	During Programming	1.8	—	1.9	V
		During Normal Operation	1.5	—	1.9	V
Digital LDO Output Setting	V_{LDODIG}	$F_{AHB} \leq 20$ MHz	1.0	—	1.9	V
		$F_{AHB} > 20$ MHz	1.2	—	1.9	V
Analog LDO Output Setting During Normal Operation[6]	V_{LDOANA}		1.8			V

Notes:

1. See reference manual for recommended inductors.
2. Recommended: X7R or X5R ceramic capacitors with low ESR. Example: Murata GRM21BR71C225K with ESR < 10 mΩ (@ frequency > 1 MHz).
3. Input voltage specification accounts for the internal LDO dropout voltage under the maximum load condition to ensure that the LDO output voltage will remain at a valid level as long as V_{LDOIN} is at or above the specified minimum.
4. The memory LDO output should always be set equal to or lower than the output of the analog LDO. When lowering both LDOs (for example to go into PM8 under low supply conditions), first adjust the memory LDO and then the analog LDO. When raising the output of both LDOs, adjust the analog LDO before adjusting the memory LDO.
5. Output range represents the programmable output range, and does not reflect the minimum voltage under all conditions. Dropout when the input supply is close to the output setting is normal, and accounted for.
6. Analog peripheral specifications assume a 1.8 V output on the analog LDO.

Table 3.6. Flash Memory

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Write Time[1]	t_{WRITE}	One 16-bit Half Word	20	21	22	µs
Erase Time[1]	t_{ERASE}	One Page	20	21	22	ms
	t_{ERALL}	Full Device	20	21	22	ms
Endurance (Write/Erase Cycles)	N_{WE}		20k	100k	—	Cycles
Retention[2]	t_{RET}	T_A = 25 °C, 1k Cycles	10	100	—	Years

Notes:
1. Does not include sequencing time before and after the write/erase operation, which may take up to 35 µs. During sequential write operations, this extra time is only taken prior to the first write and after the last write.
2. Additional Data Retention Information is published in the Quarterly Quality and Reliability Report.

Table 3.7. Internal Oscillators

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Phase-Locked Loop (PLL0OSC)						
Calibrated Output Frequency (Free-running output mode, RANGE = 2)	$f_{PLL0OSC}$	Full Temperature and Supply Range	48.3	49	49.7	MHz
Power Supply Sensitivity (Free-running output mode, RANGE = 2)	$PSS_{PLL0OSC}$	T_A = 25 °C, Fout = 49 MHz	—	300	—	ppm/V
Temperature Sensitivity (Free-running output mode, RANGE = 2)	$TS_{PLL0OSC}$	V_{BAT} = 3.3 V, Fout = 49 MHz	—	50	—	ppm/°C
Adjustable Output Frequency Range	$f_{PLL0OSC}$		23	—	50	MHz
Lock Time	$t_{PLL0LOCK}$	f_{REF} = 20 MHz, $f_{PLL0OSC}$ = 50 MHz M=39, N=99, LOCKTH = 0	—	2.75	—	µs
		f_{REF} = 2.5 MHz, $f_{PLL0OSC}$ = 50 MHz M=19, N=399, LOCKTH = 0	—	9.45	—	µs
		f_{REF} = 32.768 kHz, $f_{PLL0OSC}$ = 50 MHz M=0, N=1524, LOCKTH = 0	—	92	—	µs
Low Power Oscillator (LPOSC0)						
Oscillator Frequency	f_{LPOSC}	Full Temperature and Supply Range	19	20	21	MHz
Divided Oscillator Frequency	f_{LPOSCD}	Full Temperature and Supply Range	2.375	2.5	2.625	MHz
Power Supply Sensitivity	PSS_{LPOSC}	T_A = 25 °C	—	0.5	—	%/V
Temperature Sensitivity	TS_{LPOSC}	V_{BAT} = 3.3 V	—	55	—	ppm/°C
Low Frequency Oscillator (LFOSC0)						
Oscillator Frequency	f_{LFOSC}	Full Temperature and Supply Range	13.4	16.4	19.7	kHz
		T_A = 25 °C, V_{BAT} = 3.3 V	15.8	16.4	17.3	kHz
Power Supply Sensitivity	PSS_{LFOSC}	T_A = 25 °C	—	2.4	—	%/V
Temperature Sensitivity	TS_{LFOSC}	V_{BAT} = 3.3 V	—	0.2	—	%/°C

Table 3.7. Internal Oscillators (Continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
RTC0 Oscillator (RTC0OSC)						
Missing Clock Detector Trigger Frequency	f_{RTCMCD}		—	8	15	kHz
RTC External Input CMOS Clock Frequency	$f_{RTCEXTCLK}$		0	—	40	kHz
RTC Robust Duty Cycle Range	DC_{RTC}		25	—	55	%

Table 3.8. External Oscillator

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
External Input CMOS Clock Frequency	f_{CMOS}		0*	—	50	MHz
External Crystal Frequency	f_{XTAL}		0.01	—	25	MHz
External Input CMOS Clock High Time	t_{CMOSH}		9	—	—	ns
External Input CMOS Clock Low Time	t_{CMOSL}		9	—	—	ns
Low Power Mode Charge Pump Supply Range (input from V_{BAT})	V_{BAT}		2.4	—	3.8	V
***Note:** Minimum of 10 kHz when debugging.						

Table 3.9. SAR ADC

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Resolution	N_{bits}	12 Bit Mode		12		Bits
		10 Bit Mode		10		Bits
Supply Voltage Requirements (VBAT)	V_{ADC}	High Speed Mode	2.2	—	3.8	V
		Low Power Mode	1.8	—	3.8	V
Throughput Rate (High Speed Mode)	f_S	12 Bit Mode	—	—	250	ksps
		10 Bit Mode	—	—	1	Msps
Throughput Rate (Low Power Mode)	f_S	12 Bit Mode	—	—	62.5	ksps
		10 Bit Mode	—	—	250	ksps
Tracking Time	t_{TRK}	High Speed Mode	230	—	—	ns
		Low Power Mode	450	—	—	ns
SAR Clock Frequency	f_{SAR}	High Speed Mode	—	—	16.24	MHz
		Low Power Mode	—	—	4	MHz
Conversion Time	t_{CNV}	10-Bit Conversion, SAR Clock = 16 MHz, APB Clock = 40 MHz		762.5		ns
Sample/Hold Capacitor	C_{SAR}	Gain = 1	—	5	—	pF
		Gain = 0.5	—	2.5	—	pF
Input Pin Capacitance	C_{IN}	High Quality Inputs	—	18	—	pF
		Normal Inputs	—	20	—	pF
Input Mux Impedance	R_{MUX}	High Quality Inputs	—	300	—	Ω
		Normal Inputs	—	550	—	Ω
Voltage Reference Range	V_{REF}		1	—	V_{BAT}	V
Input Voltage Range*	V_{IN}	Gain = 1	0	—	V_{REF}	V
		Gain = 0.5	0	—	$2xV_{REF}$	V
Power Supply Rejection Ratio	$PSRR_{ADC}$		—	70	—	dB
DC Performance						
Integral Nonlinearity	INL	12 Bit Mode	—	±1	±1.9	LSB
		10 Bit Mode	—	±0.2	±0.5	LSB
Differential Nonlinearity (Guaranteed Monotonic)	DNL	12 Bit Mode	–1	±0.7	1.8	LSB
		10 Bit Mode	—	±0.2	±0.5	LSB
Offset Error (using VREFGND)	E_{OFF}	12 Bit Mode, VREF = 2.4 V	–2	0	2	LSB
		10 Bit Mode, VREF = 2.4 V	–1	0	1	LSB

Table 3.9. SAR ADC (Continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Offset Temperature Coefficient	TC_{OFF}		—	0.004	—	LSB/°C
Slope Error	E_M		–0.07	–0.02	0.02	%
Dynamic Performance (10 kHz Sine Wave Input 1dB below full scale, Max throughput)						
Signal-to-Noise	SNR	12 Bit Mode	62	66	—	dB
		10 Bit Mode	58	60	—	dB
Signal-to-Noise Plus Distortion	SNDR	12 Bit Mode	62	66	—	dB
		10 Bit Mode	58	60	—	dB
Total Harmonic Distortion (Up to 5th Harmonic)	THD	12 Bit Mode	—	78	—	dB
		10 Bit Mode	—	77	—	dB
Spurious-Free Dynamic Range	SFDR	12 Bit Mode	—	–79	—	dB
		10 Bit Mode	—	–74	—	dB
***Note:** Absolute input pin voltage is limited by the lower of the supply at VBAT and VIO.						

Table 3.10. IDAC

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static Performance						
Resolution	N_{bits}			10		Bits
Integral Nonlinearity	INL		—	±0.5	±2	LSB
Differential Nonlinearity (Guaranteed Monotonic)	DNL		—	±0.5	±1	LSB
Output Compliance Range	V_{OCR}		—	—	V_{BAT} – 1.0	V
Full Scale Output Current	I_{OUT}	2 mA Range, T_A = 25 °C	1.98	2.046	2.1	mA
		1 mA Range, T_A = 25 °C	0.99	1.023	1.05	mA
		0.5 mA Range, T_A = 25 °C	491	511.5	525	µA
Offset Error	E_{OFF}		—	250	—	nA
Full Scale Error Tempco	TC_{FS}	2 mA Range	—	100	—	ppm/°C
VBAT Power Supply Rejection Ratio		2 mA Range	—	–220	—	ppm/V
Test Load Impedance (to V_{SS})	R_{TEST}		—	1	—	kΩ
Dynamic Performance						
Output Settling Time to 1/2 LSB		min output to max output	—	1.2	—	µs
Startup Time			—	3	—	µs

Table 3.11. ACCTR (Advanced Capture Counter)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
LC Comparator Response Time, CMPMD = 11 (Highest Speed)	t_{RESP0}	+100 mV Differential	—	100	—	ns
		–100 mV Differential	—	150	—	ns
LC Comparator Response Time, CMPMD = 00 (Lowest Power)	t_{RESP3}	+100 mV Differential	—	1.4	—	µs
		–100 mV Differential	—	3.5	—	µs
LC Comparator Positive Hysteresis Mode 0 (CPMD = 11)	HYS_{CP+}	CMPHYP = 00	—	0.37	—	mV
		CMPHYP = 01	—	7.9	—	mV
		CMPHYP = 10	—	16.7	—	mV
		CMPHYP = 11	—	32.8	—	mV
LC Comparator Negative Hysteresis Mode 0 (CPMD = 11)	HYS_{CP-}	CMPHYN = 00	—	0.37	—	mV
		CMPHYN = 01	—	–7.9	—	mV
		CMPHYN = 10	—	–16.1	—	mV
		CMPHYN = 11	—	–32.7	—	mV
LC Comparator Positive Hysteresis Mode 1 (CPMD = 10)	HYS_{CP+}	CMPHYP = 00	—	0.47	—	mV
		CMPHYP = 01	—	5.85	—	mV
		CMPHYP = 10	—	12	—	mV
		CMPHYP = 11	—	24.4	—	mV
LC Comparator Negative Hysteresis Mode 1 (CPMD = 10)	HYS_{CP-}	CMPHYN = 00	—	0.47	—	mV
		CMPHYN = 01	—	–6.0	—	mV
		CMPHYN = 10	—	–12.1	—	mV
		CMPHYN = 11	—	–24.6	—	mV
LC Comparator Positive Hysteresis Mode 2 (CPMD = 01)	HYS_{CP+}	CMPHYP = 00	—	0.66	—	mV
		CMPHYP = 01	—	4.55	—	mV
		CMPHYP = 10	—	9.3	—	mV
		CMPHYP = 11	—	19	—	mV
LC Comparator Negative Hysteresis Mode 2 (CPMD = 01)	HYS_{CP-}	CMPHYN = 00	—	0.6	—	mV
		CMPHYN = 01	—	–4.5	—	mV
		CMPHYN = 10	—	–9.5	—	mV
		CMPHYN = 11	—	–19	—	mV

Table 3.11. ACCTR (Advanced Capture Counter) (Continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
LC Comparator Positive Hysteresis Mode 3 (CPMD = 00)	HYS_{CP+}	CMPHYP = 00	—	1.37	—	mV
		CMPHYP = 01	—	3.8	—	mV
		CMPHYP = 10	—	7.8	—	mV
		CMPHYP = 11	—	15.6	—	mV
LC Comparator Negative Hysteresis Mode 3 (CPMD = 00)	HYS_{CP-}	CMPHYN = 00	—	1.37	—	mV
		CMPHYN = 01	—	–3.9	—	mV
		CMPHYN = 10	—	–7.9	—	mV
		CMPHYN = 11	—	–16	—	mV
LC Comparator Input Range (ACCTR0_LCIN pin)	V_{IN}		–0.25	—	V_{BAT} + 0.25	V
LC Comparator Common-Mode Rejection Ratio	$CMRR_{CP}$		—	75	—	dB
LC Comparator Power Supply Rejection Ratio	$PSRR_{CP}$		—	72	—	dB
LC Comparator Input Offset Voltage	V_{OFF}	T_A = 25 °C	–10	0	10	mV
LC Comparator Input Offset Tempco	TC_{OFF}		—	3.5	—	µV/°C
Reference DAC Offset Error	DAC_{EOFF}		–1	—	1	LSB
Reference DAC Full Scale Output	DAC_{FS}	Low Range	—	V_{IO}/8	—	V
		High Range	—	V_{IO}	—	V
Reference DAC Step Size	DAC_{LSB}	Low Range (48 steps)	—	V_{IO}/384	—	V
		High Range (64 steps)	—	V_{IO}/64	—	V
LC Oscillator Period	T_{LCOSC}		—	25	—	ns
LC Bias Output Impedance	R_{LCBIAS}	10 µA Load	—	1	—	kΩ
LC Bias Drive Strength	I_{LCBIAS}		—	—	2	mA
Pull-Up Resistor Tolerance	R_{TOL}	PUVAL[4:2] = 0 to 6	-15	—	15	%
		PUVAL[4:2] = 7	-10	—	10	%